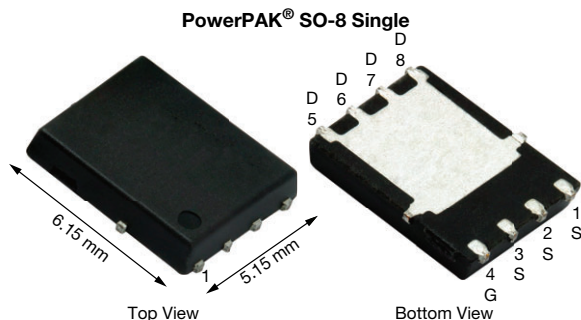


N-Channel 250 V (D-S) MOSFET



FEATURES

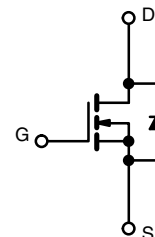
- TrenchFET® power MOSFET
- Low thermal resistance PowerPAK® package
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Primary side switch
- Synchronous rectification
- DC/DC converter
- Lighting
- Industrial



N-Channel MOSFET

PRODUCT SUMMARY

V _{DS} (V)	250
R _{DS(on)} max. (Ω) at V _{GS} = 10 V	0.150
R _{DS(on)} max. (Ω) at V _{GS} = 7.5 V	0.170
Q _g typ. (nC)	8.6
I _D (A)	12.3 ^f
Configuration	Single

ORDERING INFORMATION

Package	PowerPAK SO-8
Lead (Pb)-free and halogen-free	Si7434ADP-T1-RE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	250	V
Gate-source voltage	V _{GS}	± 20	V
Continuous drain current (T _J = 150 °C)	I _D	T _C = 25 °C	12.3
		T _C = 70 °C	9.8
		T _A = 25 °C	3.7 ^{a, b}
		T _A = 70 °C	3 ^{a, b}
Pulsed drain current (t = 100 μs)	I _{DM}	25	A
Continuous source-drain diode current	I _S	T _C = 25 °C	45
		T _A = 25 °C	4.2 ^{a, b}
Single pulse avalanche current	I _{AS}	12	A
Single pulse avalanche energy	E _{AS}	7.2	mJ
Maximum power dissipation	P _D	T _C = 25 °C	54.3
		T _C = 70 °C	34.8
		T _A = 25 °C	5 ^{a, b}
		T _A = 70 °C	3.2 ^{a, b}
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^a		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	R _{thJA}	20	25	°C/W
Maximum junction-to-case (drain)	R _{thJC}	1.8	2.3	

Notes

- Surface mounted on 1" x 1" FR4 board
- t = 10 s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 65 °C/W
- T_C = 25 °C



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	250	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = 250 μA	-	254	-	mV/°C
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J		-	-6.9	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2	-	4	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 250 V, V _{GS} = 0 V, T _J = 70 °C	-	-	10	
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	10	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 3.7 A	-	0.125	0.150	Ω
		V _{GS} = 7.5 V, I _D = 3.5 A	-	0.135	0.170	
Forward transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 3.7 A	-	10	-	S
Dynamic ^b						
Input capacitance	C _{iss}	V _{DS} = 125 V, V _{GS} = 0 V, f = 1 MHz	-	600	-	pF
Output capacitance	C _{oss}		-	65	-	
Reverse transfer capacitance	C _{rss}		-	2	-	
Total gate charge	Q _g	V _{DS} = 125 V, V _{GS} = 10 V, I _D = 2 A	-	10.9	16.5	nC
		V _{DS} = 125 V, V _{GS} = 7.5 V, I _D = 2 A	-	8.6	12.9	
Gate-source charge	Q _{gs}		-	2.7	-	
Gate-drain charge	Q _{gd}		-	2.9	-	
Output charge	Q _{oss}	V _{DS} = 125 V, V _{GS} = 0 V	-	30	45	
Gate resistance	R _g	f = 1 MHz	0.5	2.3	4.6	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = 125 V, R _L = 41.7 Ω, I _D ≅ 3 A, V _{GEN} = 10 V, R _g = 1 Ω	-	8	16	ns
Rise time	t _r		-	22	35	
Turn-off delay time	t _{d(off)}		-	18	30	
Fall time	t _f		-	22	35	
Turn-on delay time	t _{d(on)}	V _{DD} = 125 V, R _L = 41.7 Ω, I _D ≅ 3 A, V _{GEN} = 7.5 V, R _g = 1 Ω	-	10	20	
Rise time	t _r		-	22	40	
Turn-off delay time	t _{d(off)}		-	18	30	
Fall time	t _f		-	25	50	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	45	A
Pulse diode forward current	I _{SM}		-	-	25	
Body diode voltage	V _{SD}	I _S = 3.4 A, V _{GS} = 0 V	-	0.8	1.2	V
Body diode reverse recovery time	t _{rr}	I _F = 3.4 A, di/dt = 100 A/μs, T _J = 25 °C	-	100	150	ns
Body diode reverse recovery charge	Q _{rr}		-	356	550	nC
Reverse recovery fall time	t _a		-	65	-	ns
Reverse recovery rise time	t _b		-	35	-	

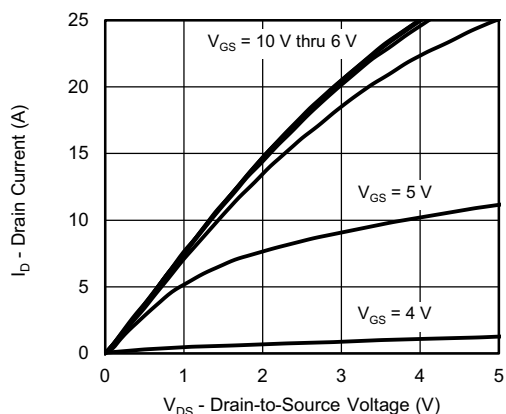
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

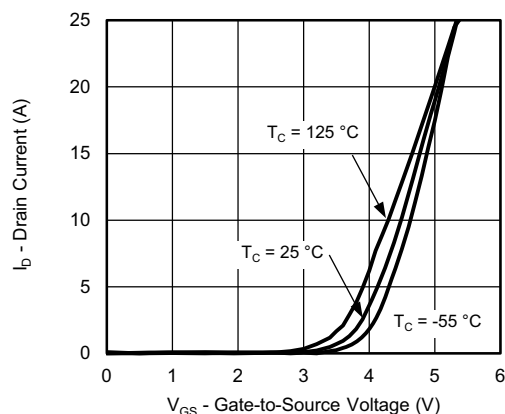
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



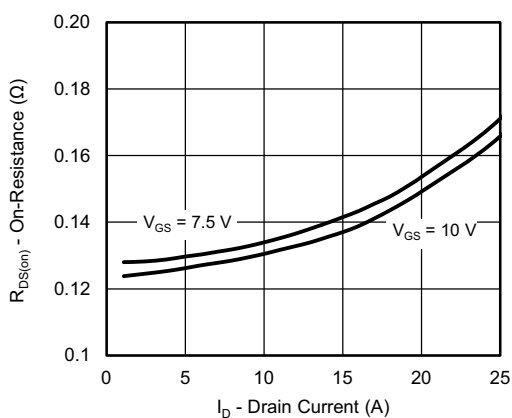
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



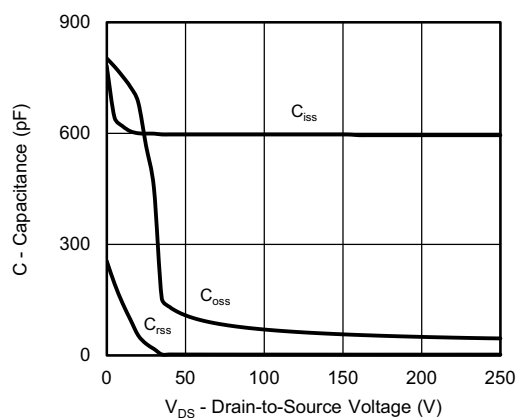
Output Characteristics



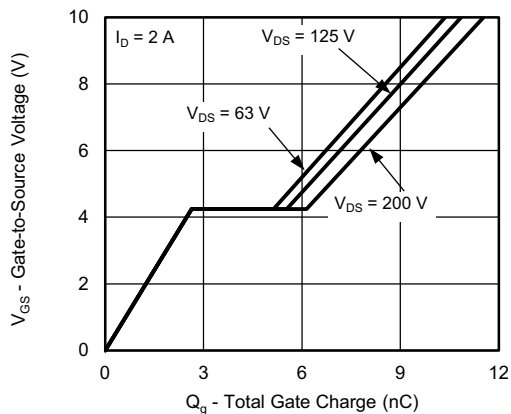
Transfer Characteristics



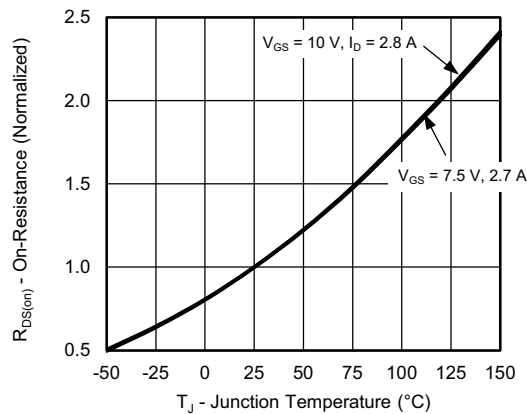
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



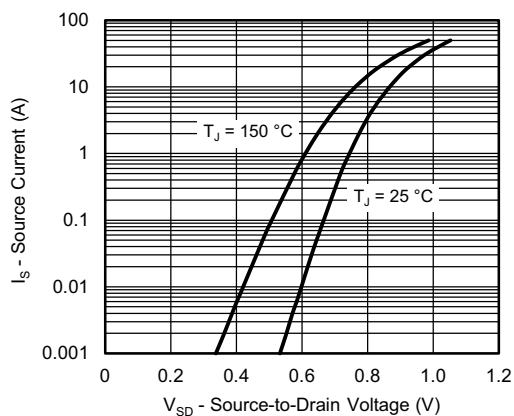
Gate Charge



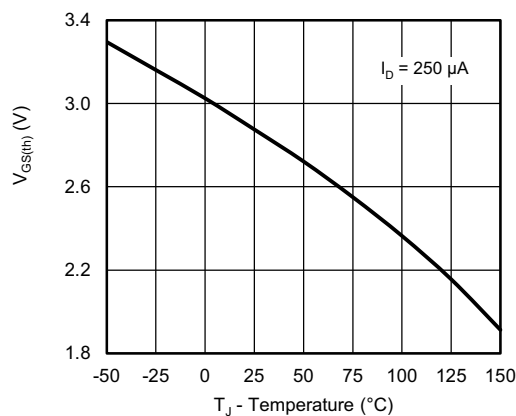
On-Resistance vs. Junction Temperature



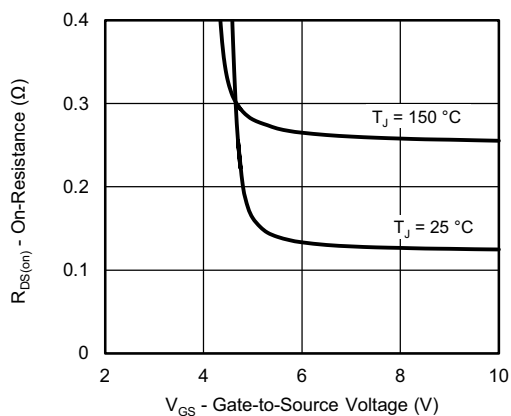
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



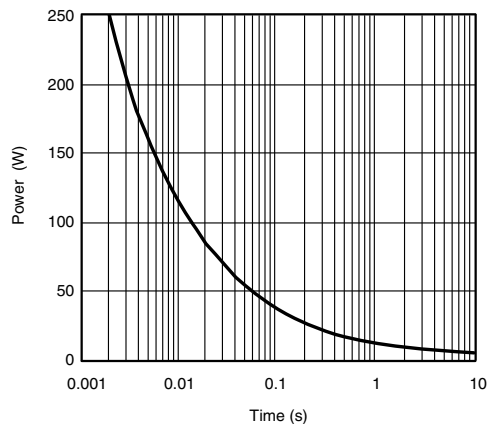
Source-Drain Diode Forward Voltage



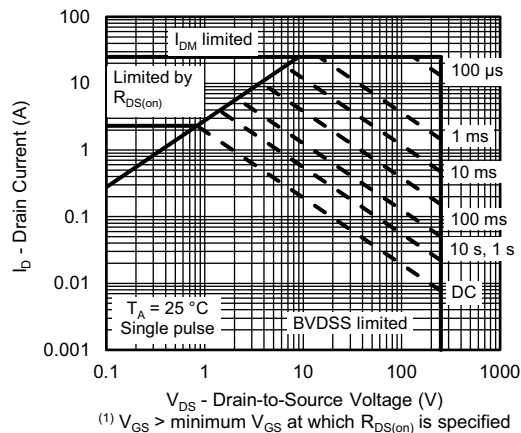
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



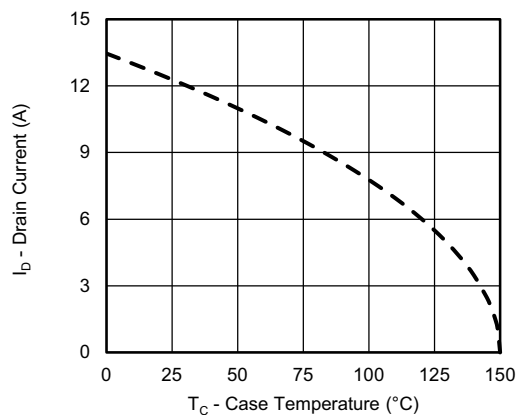
Single Pulse Power, Junction-to-Ambient



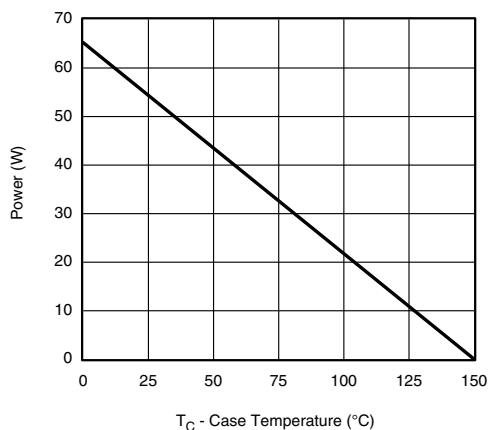
Safe Operating Area, Junction-to-Ambient



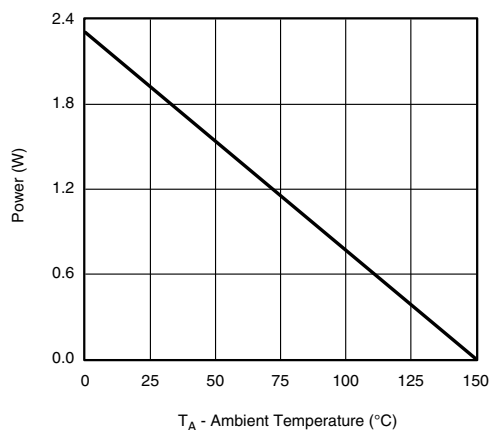
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



Power, Junction-to-Case



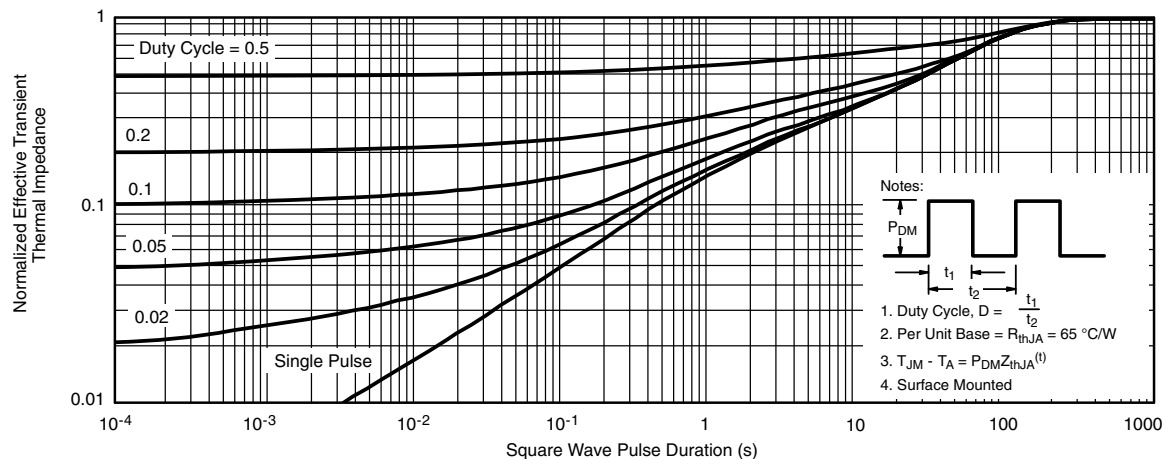
Power, Junction-to-Ambient

Note

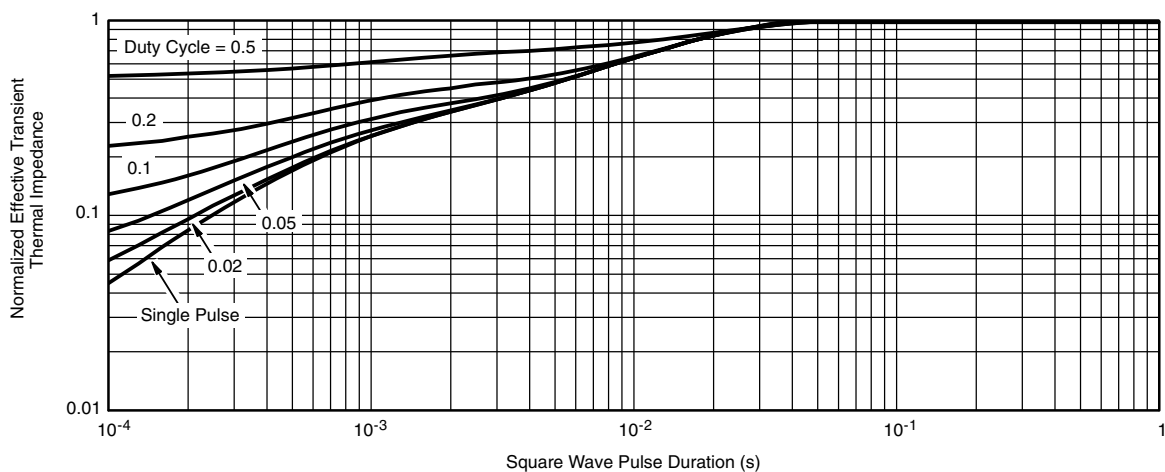
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9